

Synthesis of VO_2 Nanowire and Observation of the Metal-Insulator Transition

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We have fabricated crystalline nanowires of VO_2 using a new synthetic method. A nanowire synthesized at 650 °C shows the semiconducting behavior and a nanowire at 670 °C exhibits the first-order metal-insulator transition which is not the one-dimensional property. The temperature coefficient of resistance in the semiconducting nanowire is 7.06 %/K at 300 K, which is higher than that of commercial bolometer.

One-dimensional (1-D) nanostructure materials exhibit unique physical properties that differ from their bulk properties. It is due to a characteristic of the 1-D structure such as nanotubes, nanorods, and nanowires [1-3]. It is well-known that an abrupt metal-insulator transition (MIT) and a hysteresis behavior do not occur in 1-D structure. These are an advantage for a device application. Therefore, synthetic efforts for 1-D materials have been continued by many researchers, although synthesis of 1-D structures is very difficult.

The transition oxide material, VO_2 , undergoes the structural phase transition (SPT) from the monoclinic to the rutile tetragonal structures near 340 K. It was revealed that the first-order MIT is controlled by hole doping of a low density and is not caused by the SPT; this demonstrated the Mott transition [4]. VO_2 has a lot of applications such as electro-optic switch, infrared bolometer, and the Mott first-order field effect transistor (FET), etc. New ideas for the first-order MIT transistor were disclosed by Kim and Kang [5] and Chudnovskii et al. [6]. For the fabrication of nanometer-scale Mott FET devices, the synthesis of single-crystalline VO_2 nanowires was reported [7]. Metastable VO_2 nanowire arrays were synthesized via an ethylene glycol reduction approach [8].

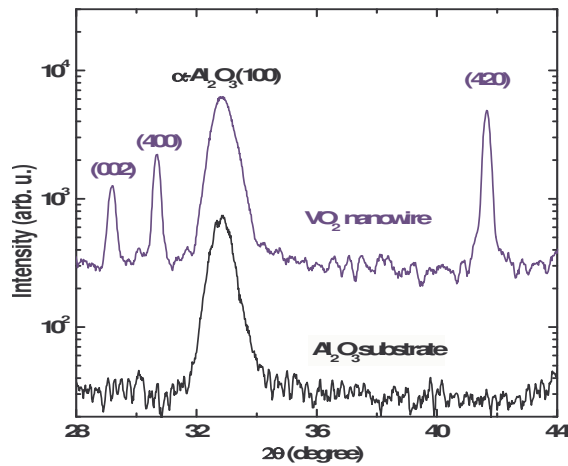


FIG. 1. The crystal structure of a VO_2 nanowire grown at 670 °C for 30 minutes. XRD pattern of the VO_2 nanowire compared to JCPDS.

In this paper, we report synthesizing conditions of VO_2 nanowires fabricated by using a synthetic method. Their electrical characteristics are analyzed by measuring the temperature dependence of resistance and I-V characteristics. In particular, to our knowledge, we first observed first-order MITs in nanowires.

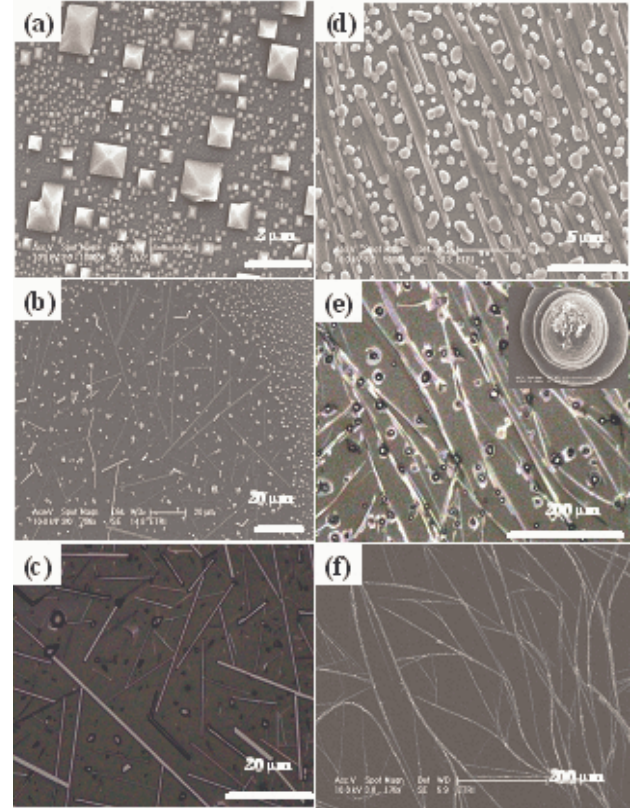


FIG. 2. SEM images of VO_2 nanostructures. The annealing temperatures and times are as follows: (a) 630 °C, (b) 650 °C, (c) 670 °C for 30 min, and (d) 40 min, (e) 50 min, (f) 60 min at 670 °C.

VO_2 nanostructures with nanoblock and nanowire were successfully synthesized by controlling the oxygen partial pressure in the oxidation process of metallic vanadium. The metallic vanadium was grown on $\alpha\text{-Al}_2\text{O}_3$ (01-10) substrate at 500 °C in an Ar ambient atmosphere.

of 50 m Torr using RF Sputter. Advantage of this new method is a shorter synthesis time than that of other nanowire fabrication methods such as thermal chemical vapor deposition [9] and the bulk crystal growth method [6]. The use of Al_2O_3 substrate different from SiO_2/Si derived more high quality nanowire on the basis of the fact that VO_2 film is well-grown on Al_2O_3 . Annealing was performed at 630–670 C in the O_2 ambient atmosphere of 50 m Torr for 30–60 minutes. Figure 1 shows an X-ray diffraction (XRD) pattern of the crystal structure of a VO_2 nanowire grown at 630 C for 30 minutes. Lattice constants from XRD peaks are calculated as $a = 12.03$ Å, $b = 6.693$ Å, $c = 6.42$ Å, which is in agreement with the reported values of the monoclinic VO_2 for JCPDS (card No. 71-0042) [10]. (400) peak is the most intense peak of typical VO_2 thin film grown on Al_2O_3 substrate. The XRD peaks indicate that the VO_2 nanowire is crystalline.

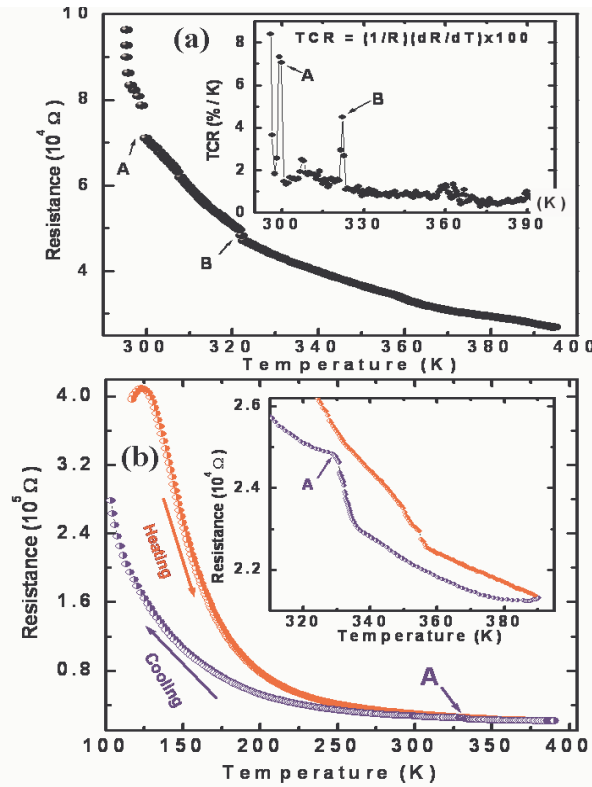


FIG. 3. (a) Temperature dependence of resistance of the VO_2 nanowire grown at 650 C. Inset shows the Temperature Coefficient of Resistance; $\text{TCR} = -(1/R) (dR/dT) 100$. (b) The hysteresis of temperature dependence of resistance of the VO_2 nanowire. Inset is magnification of resistances around 330 K.

Figure 2 (a)–(c) show high resolution scanning electron microscopy (SEM) images of nanostructures synthesized at several annealing temperatures. The nanostructures are the semiball nanoblocks (quadrangular pyramidal) and nanowires. Nanoblocks with a size of 50–500

nm were synthesized at 630 C. Nanoblocks and wires co-exist at 650 C. Only nanowires were grown at 670 C. The nanowires in Fig. 2 (c) are rectangular parallelepiped form with a length of 10–800 nm (z-axis), a width of 20–150 nm (y-axis) and a thickness of 100–500 nm (x-axis).

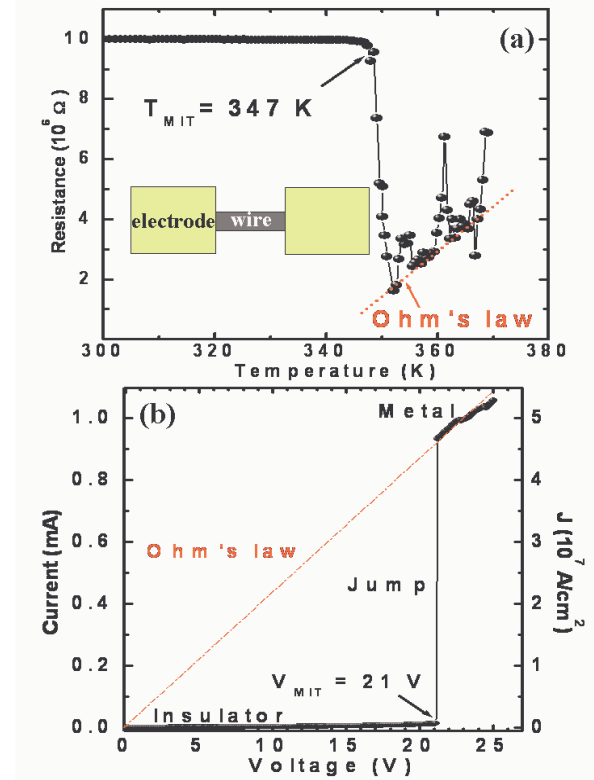


FIG. 4. (a) Temperature dependence of resistance of VO_2 nanowire of grown at 670 C. Inset shows electrode. (b) I-V measurement of VO_2 nanowire. It shows a sharp current jump when an electrical field is applied to nanowire with 21 V.

Annealing time for fabrication of good nanowires was also changed from 40 to 60 minutes with step of 10 minute, as shown in Fig. 2 (d)–(f). When annealing time was 40 min in (Fig. 2 (d)), nanowires begin to connect with a neighbor nanowire, and it appears a small nanoblock like a cone form. The inset in Fig. 2 (e), it shows a clearly cone form. Annealing time was 1 hour, a nanowire is connected to other nanowires like a crooked bough, as shown in Fig. 2 (f). Thus, the optimum growth condition of VO_2 nanowires on Al_2O_3 substrate is found to be at 670 C and 30 min.

We measured the temperature dependence of resistance and I-V characteristic curves to reveal electrical properties of VO_2 nanowires. Figure 3 shows the temperature dependence of resistance and hysteresis curve for the VO_2 nanowires grown at 650 C. The temperature dependence is semiconductive and has no the MIT jump (abrupt change in resistance with temperature) which is the resistance characteristic of VO_2 . Moreover, the tem-

perature coefficient of resistance (TCR) has large values near 300 K and below 320 K (inset in Fig. 3 (a)). A TCR value at 300 K is 7.06 %/K, which is larger than that of a commercial bolometer, as indicated by arrow A in Fig. 3(a). A TCR peak near 320 K is due to a change of the resistance near 320 K, as indicated by arrow B. Figure 3(b) shows a lower resistance than that at 300 K in Fig. 3(a) and the semiconducting temperature behavior in the heating process. Hysteresis in the heating and cooling process is exhibited. In the cooling process, a small step of the resistance near 330 K appears, as indicated by arrow A in the inset of Fig. 3(b), which can be regarded as the first-order MIT in VO₂. This is attributed to hole excitation by heating produced in the cooling process from a high temperature of 390 K, on the grounds that the first-order MIT occurs by hole excitation [4]. The fact that the magnitude of the jump is small is due to a large resistance in the nanowire because the large resistance reduces the magnitude of jump [5].

For the VO₂ nanowire grown at 670 °C, the sharp first-order MIT jump near 347 K and the ohmic behavior above 347 K are exhibited (Fig. 4(a)). The electric field-induced first-order MIT is also measured (Fig. 4(b)). Jump of current is 1.2×10^{-5} A to 9×10^{-4} A at $V_{MIT} = 21$ V and current follows Ohm's law in the larger voltage than V_{MIT} . This indicates that the nanowire has a component of metal. The MIT voltage can be controlled by varying the distance between electrodes of nanowire. The observed first-order MITs are attributed to breakdown of the critical on-site Coulomb interaction between electrons [4,11].

In summary, we found conditions fabricating nanowires showing the first-order MIT which is far from the 1-D structural property. Furthermore, the crystalline nanowires with large resistance are useful to a lot of device applications.

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